

CoolMOS™ Power Transistor

Features

- Lowest figure of merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Pb-free lead plating; RoHS compliant; **available in Halogen free mold compound^{a)}**
- Qualified for industrial grade applications according to JEDEC¹⁾
 - ^{a)} non-Halogen free (OPN: IPS50R520CPBT);
 - Halogen free (OPN: IPS50R520CPAT)

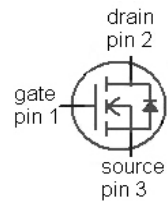
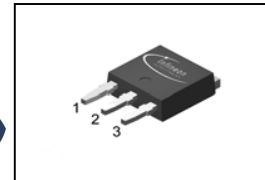
CoolMOS CP is specially designed for:

- Hard and softswitching SMPS for server power supplies
- DCM PFC for Lamp Ballast
- PWM-Stages Lamp Ballast, LCD and PDP TV

Product Summary

$V_{DS} @ T_{jmax}$	550	V
$R_{DS(on),max}$	0.520	Ω
$Q_{g,typ}$	13	nC

PG-TO251



Type	Package	Marking
IPS50R520CP	PG-TO251	5R520P

Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25^\circ\text{C}$	7.1	A
		$T_C=100^\circ\text{C}$	4.5	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	15	
Avalanche energy, single pulse	E_{AS}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	166	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	E_{AR}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	0.25	
Avalanche current, repetitive $t_{AR}^{2),3)}$	I_{AR}		2.5	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\ldots 400\text{ V}$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f > 1\text{ Hz}$)	± 30	
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	66	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^\circ\text{C}$
Mounting torque		M3 and M3.5 screws	60	Ncm

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	3.8	A
Diode pulse current ⁽²⁾	$I_{S,pulse}$		15	
Reverse diode dv/dt ⁽⁴⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.9	K/W
Thermal resistance, junction - ambient	R_{thJA}	lead	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{solder}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{ mA}$	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=500\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	1	μA
		$V_{DS}=500\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=3.8\text{ A}, T_j=25\text{ °C}$	-	0.47	0.52	Ω
		$V_{GS}=10\text{ V}, I_D=3.8\text{ A}, T_j=150\text{ °C}$	-	1.20	-	
Gate resistance	R_G	$f=1\text{ MHz}, \text{open drain}$	-	2.2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	680	-	pF
Output capacitance	C_{oss}		-	31	-	
Effective output capacitance, energy related ⁵⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 400 V	-	29	-	
Effective output capacitance, time related ⁶⁾	$C_{o(tr)}$		-	63	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=3.8\text{ A},$ $R_G=48.3\ \Omega$	-	35	-	ns
Rise time	t_r		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	80	-	
Fall time	t_f		-	17	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}, I_D=3.8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3	-	nC
Gate to drain charge	Q_{gd}		-	5	-	
Gate charge total	Q_g		-	13	17	
Gate plateau voltage	$V_{plateau}$		-	5.2	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=3.8\text{ A},$ $T_j=25\text{ °C}$	-	0.9	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	240	-	ns
Reverse recovery charge	Q_{rr}		-	1.6	-	μC
Peak reverse recovery current	I_{rrm}		-	13	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

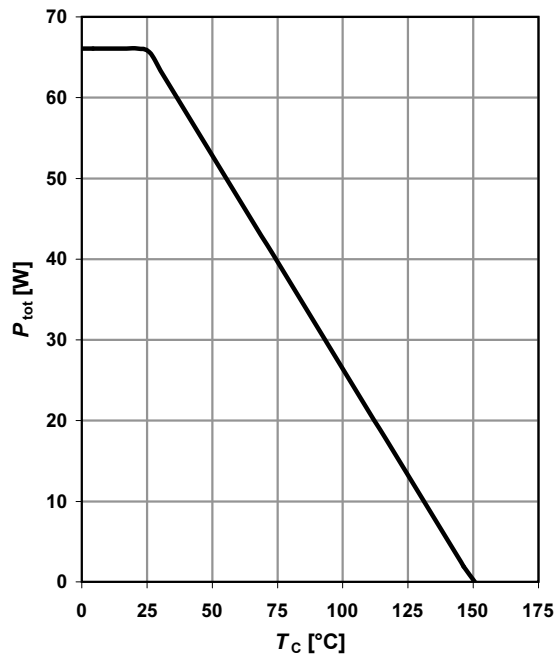
⁴⁾ $I_{SD} \leq I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

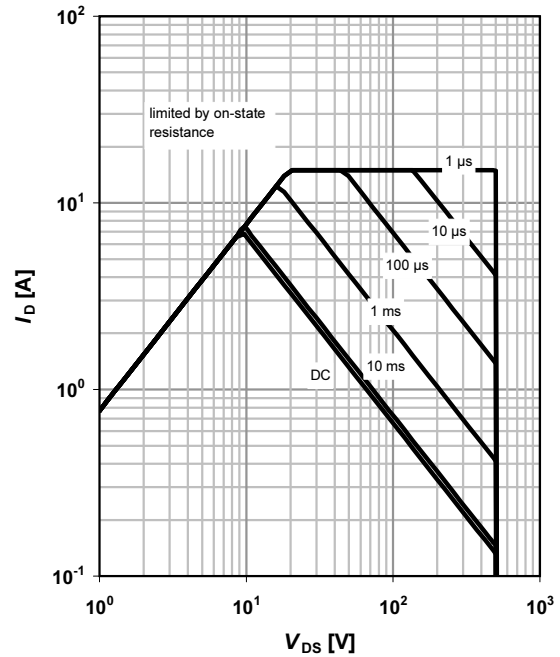
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$


2 Safe operating area

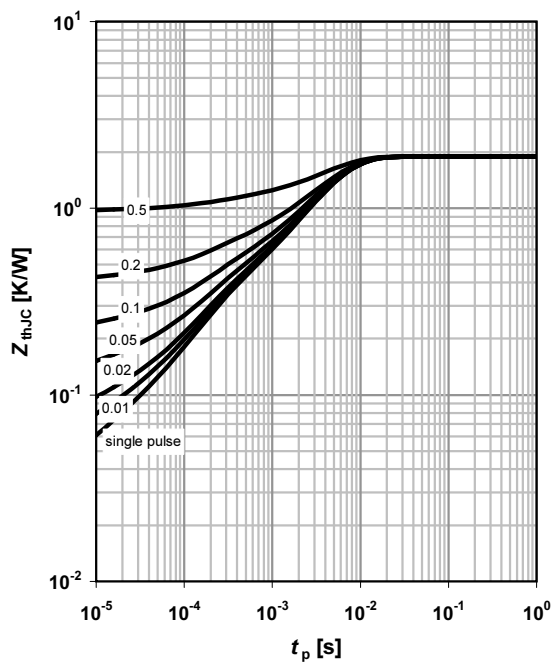
$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

parameter: t_p


3 Max. transient thermal impedance

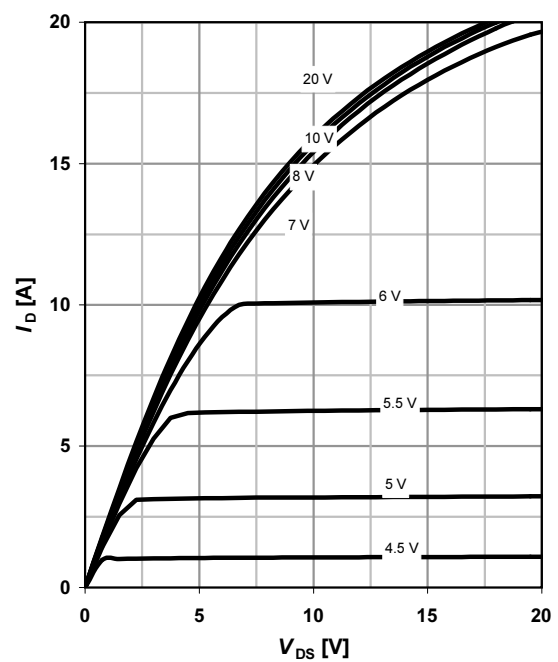
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p / T$


4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

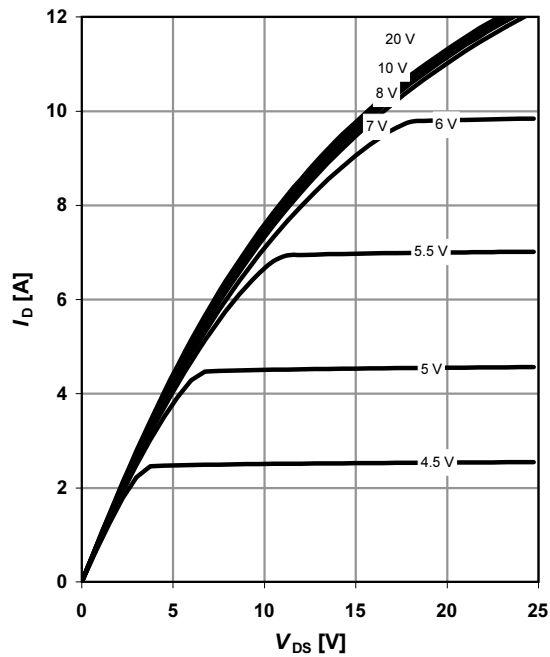
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

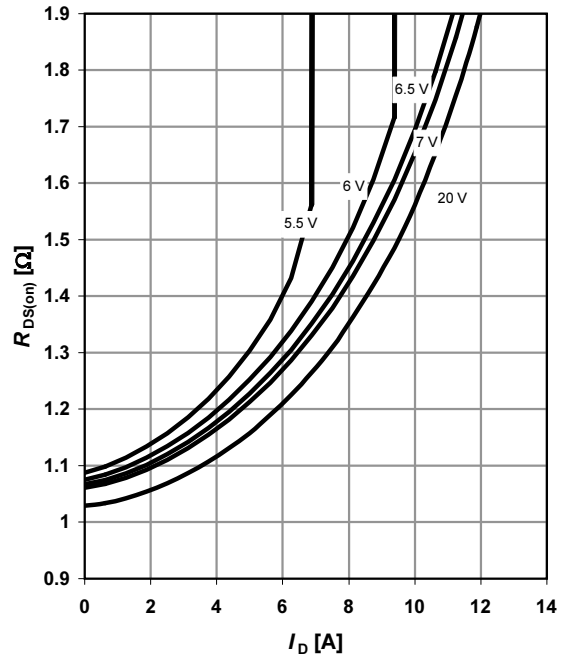
parameter: V_{GS}



6 Typ. drain-source on-state resistance

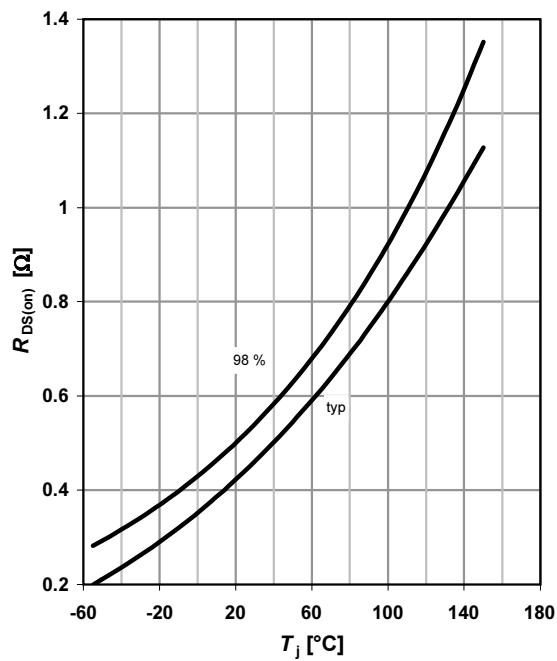
$$R_{DS(on)} = f(I_D); T_j = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

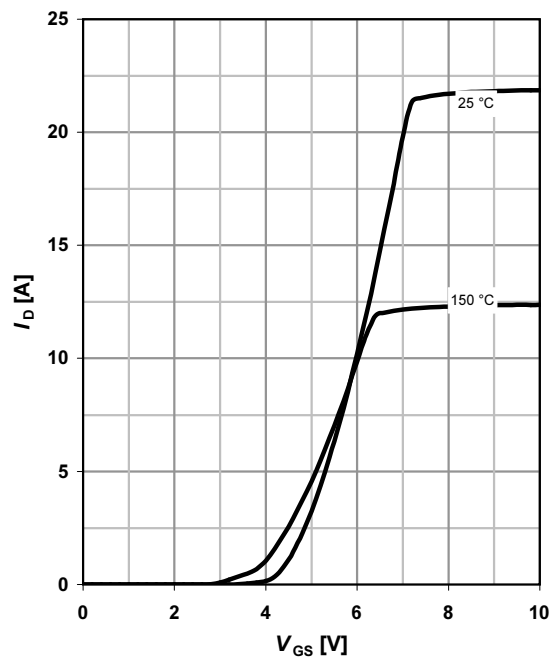
$$R_{DS(on)} = f(T_j); I_D = 3.8\text{ A}; V_{GS} = 10\text{ V}$$



8 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D| R_{DS(on)max}$$

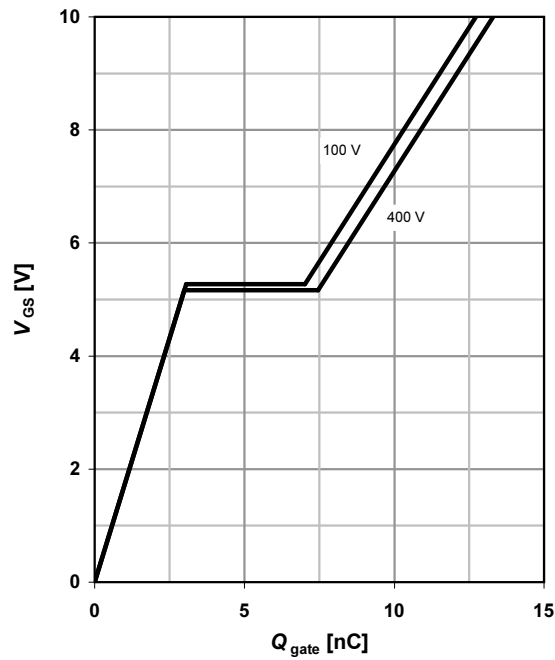
parameter: T_j



9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=3.8 \text{ A pulsed}$$

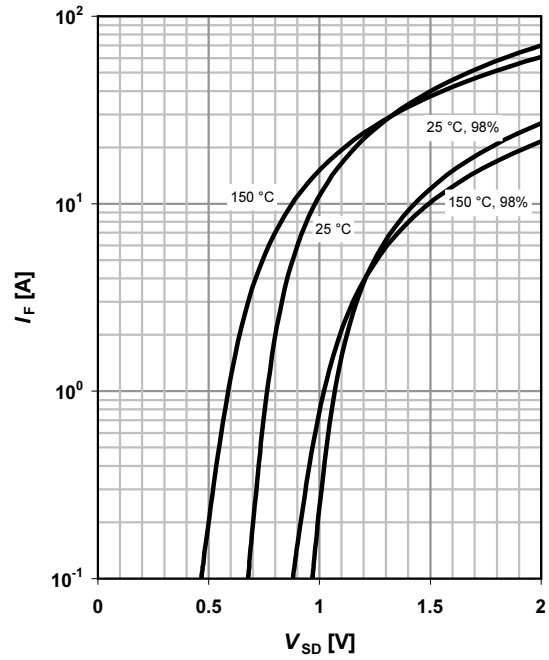
parameter: V_{DD}



10 Forward characteristics of reverse diode

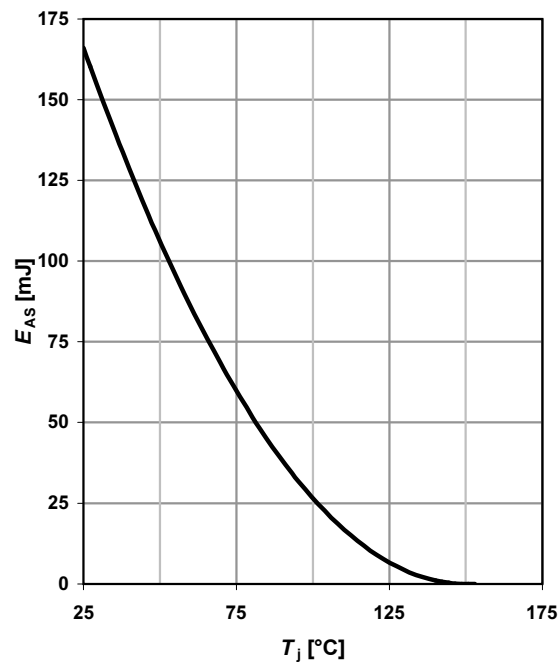
$$I_F=f(V_{SD})$$

parameter: T_j



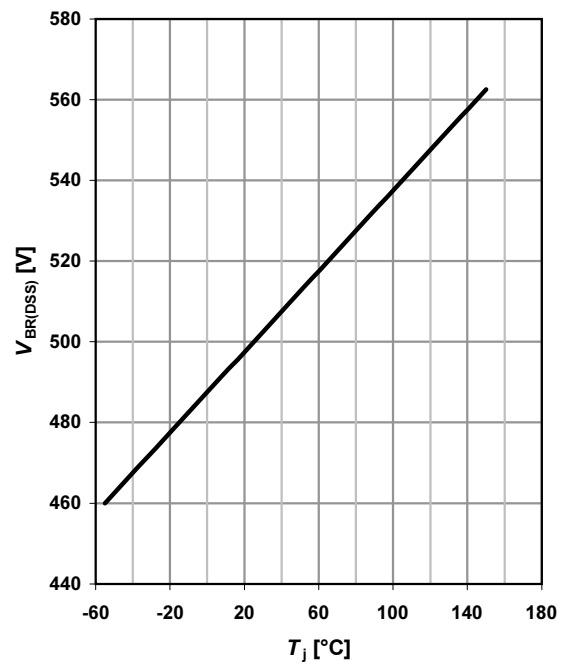
11 Avalanche energy

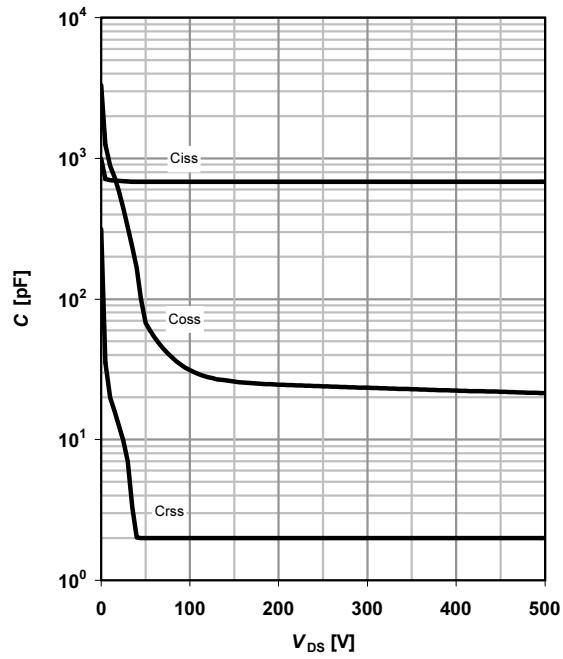
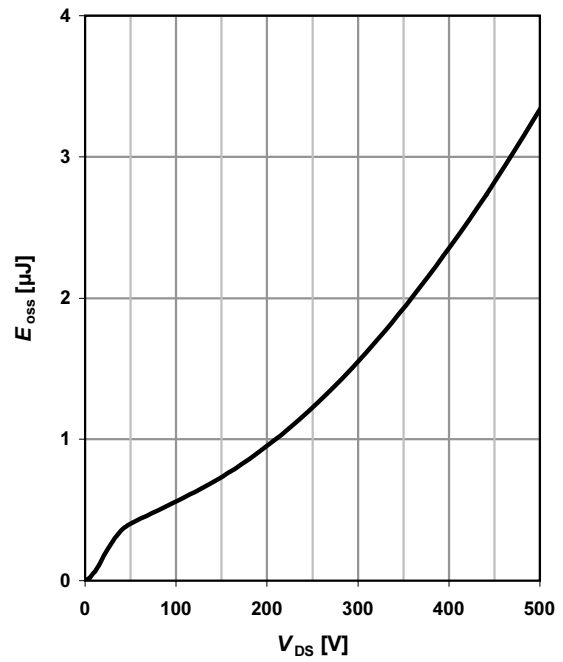
$$E_{AS}=f(T_j); I_D=2.5 \text{ A}; V_{DD}=50 \text{ V}$$



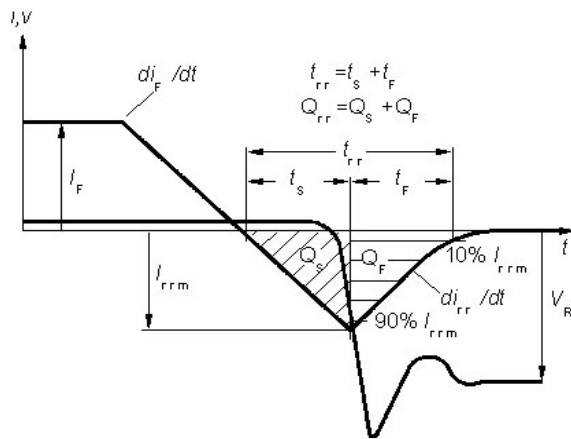
12 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$$

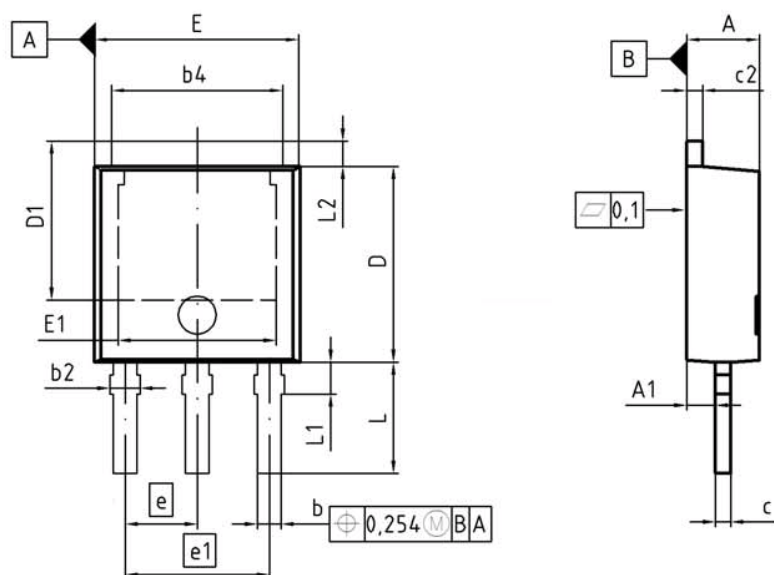


13 Typ. capacitances
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

14 Typ. Coss stored energy
 $E_{oss} = f(V_{DS})$


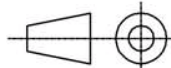
Definition of diode switching characteristics



PG-TO251-3-1-21-41 (I-PAK Short Leads)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.39	0.086	0.094
A1	0.80	1.14	0.031	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.58	0.018	0.023
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.44	0.198	0.214
E	6.35	6.73	0.250	0.265
E1	4.90	5.10	0.193	0.201
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	3.40	3.60	0.134	0.142
L1	0.90	1.10	0.035	0.043
L2	0.90	1.10	0.035	0.043

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